

GSDSS32W Series

Surface Mount Schottky Rectifiers

Product Description

Reverse Voltage 20V to 100V Forward Current 3.0A

Features

- Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity diodes in surface mount applications
- Schottky barrier junction, majority carrier conduction
- Guard ring for stress protection
- Low forward voltage drop
- High current capability
- High surge capability
- High reliability
- Lead(Pb)-Free

Mechanical Data

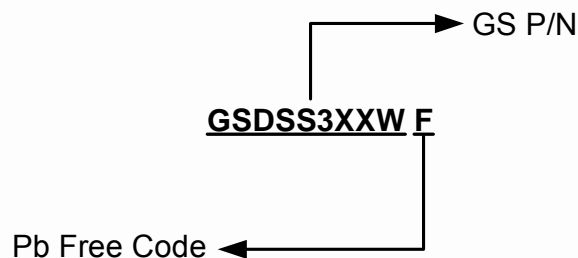
- Case : Molded plastic, SMA(W) Package
- Epoxy meets flammability requirements per UL 94V-0
- All terminal leads are readily solderable
- Weight approx : 70 mg

Packages



SMA(W)
Color Band Denotes CATHODE

Ordering Information



Part Number	Package	Quantity
GSDSS32WF Series	SMA(W)	5000 PCS

Marking Information

P/N	Part Marking	Package
GSDSS32WF	S32W	SMA(W)
GSDSS33WF	S33W	SMA(W)
GSDSS34WF	S34W	SMA(W)
GSDSS35WF	S35W	SMA(W)
GSDSS36WF	S36W	SMA(W)
GSDSS38WF	S38W	SMA(W)
GSDSS310WF	S3AW	SMA(W)

Electrical Characteristics

(Rating 25°C Ambient Temperature Unless Otherwise Specified.)

Symbol	Conditions	GSDSS32WF	GSDSS33WF	GSDSS34WF	GSDSS35WF	Unit
V_{RRM}	Maximum Recurrent Peak Reverse Voltage	20	30	40	50	V
V_{RMS}	Maximum RMS Voltage	14	21	28	35	V
V_{DC}	Maximum DC Blocking Voltage	20	30	40	50	V
V_F	Maximum Instantaneous At 3.0A DC	0.55			0.70	V
Symbol	Conditions	GSDSS36WF	GSDSS38WF	GSDSS310WF		Unit
V_{RRM}	Maximum Recurrent Peak Reverse Voltage	60	80	100		V
V_{RMS}	Maximum RMS Voltage	42	56	70		V
V_{DC}	Maximum DC Blocking Voltage	60	80	100		V
V_F	Maximum Instantaneous At 3.0A DC	0.70	0.85			V
I_R	Maximum Reverse Leakage Current at rated V_R	$T_J = 25^\circ\text{C}$	0.5			mA
		$T_J = 125^\circ\text{C}$	20			
$I_{F(AV)}$	Maximum Average Forward Rectified Current	3.0				A
I_{FSM}	Peak Forward Surge Current (8.3ms Single Half Sine-Wave)	80				A
$R_{\theta JL}$	Typical Thermal Resistance (Junction to lead)	35				$^\circ\text{C/W}$
T_J	Operating Temperature Range	-50 to +150				$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-50 to +150				$^\circ\text{C}$

Typical Characteristics

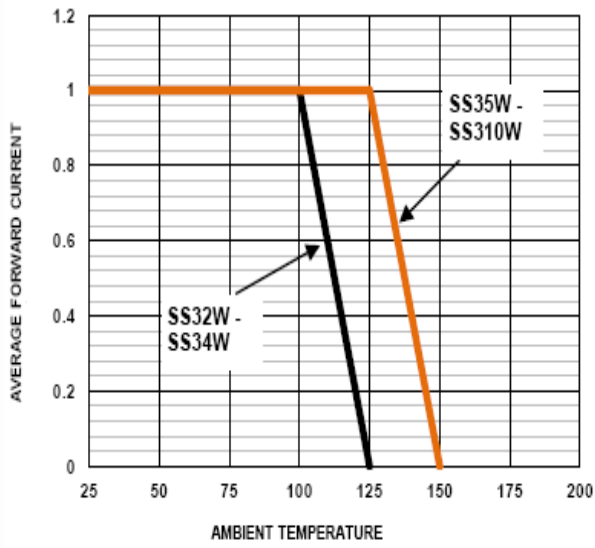


Figure 1. Forward Current Derating Curve

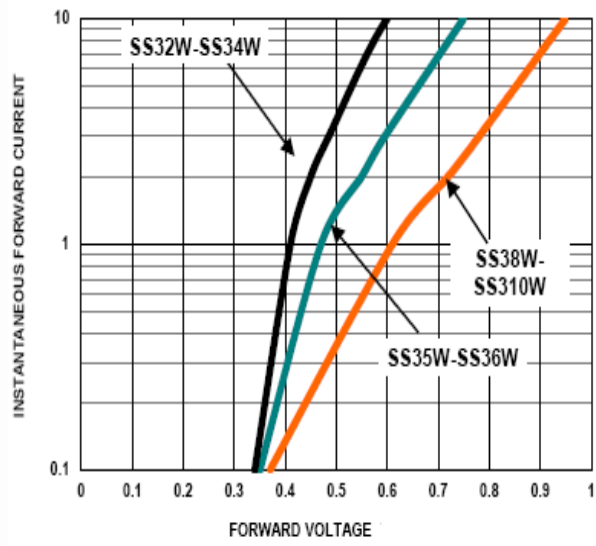


Figure 2. Forward Voltage Characteristics

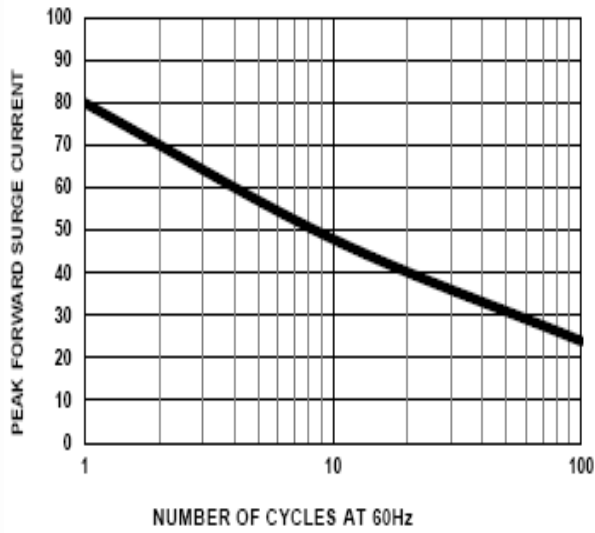


Figure 3. Non-Repetitive Surge Current

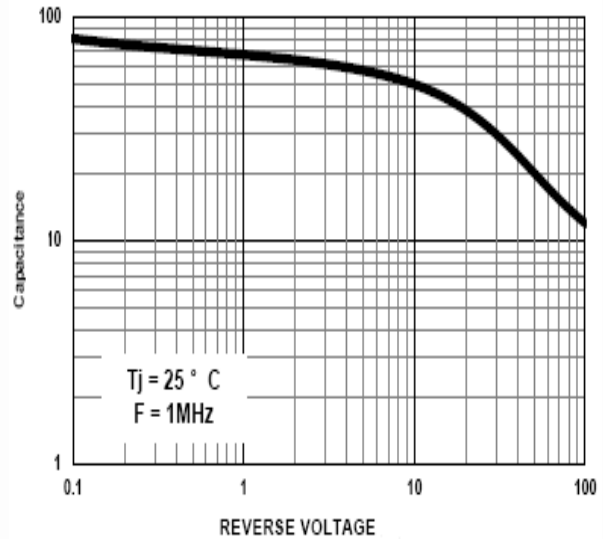
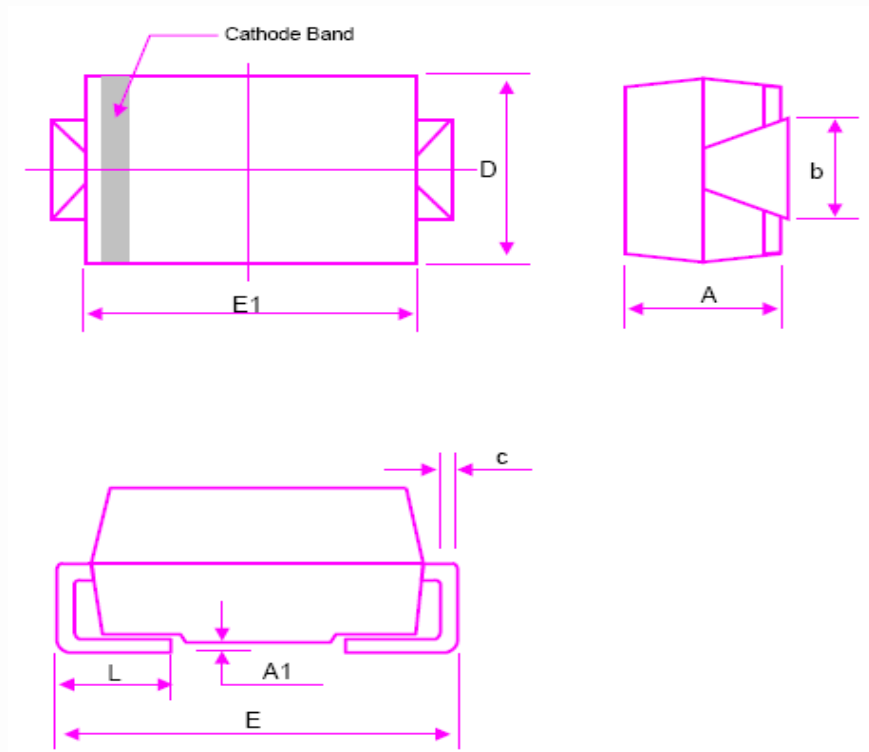


Figure 4. Junction Capacitance

Package Dimension

SMA(W)







Dimensions




Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	1.70	2.31	0.067	0.091
A1	0.10	0.20	0.004	0.008
b	1.29	1.70	0.051	0.067
c	0.15	0.31	0.006	0.012
D	2.18	2.79	0.086	0.110
E	4.70	5.31	0.185	0.209
E1	4.06	4.57	0.160	0.180
L	0.89	1.50	0.035	0.059



NOTICE

Information furnished is believed to be accurate and reliable. However Globaltech Semiconductor assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties, which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Globaltech Semiconductor. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information without express written approval of Globaltech Semiconductor.

CONTACT US

GS Headquarter	
	4F.,No.43-1,Lane11,Sec.6,Minquan E.Rd NeiHu District Taipei City 114, Taiwan (R.O.C)
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

Shenzhen Branch(China)	
	1113 B Building, Happiness Washington, Baoan Nan Road, Luohu District, Shenzhen City, China
	0755-22208941
	sales_cn@gs-power.com

RD Division	
	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587